

Silicon Carbide (SiC) Schottky Diode – EliteSiC, 10 A, 1200 V, D1, TO-247-2L

FFSH10120A-F155

Description

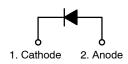
Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 100 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits

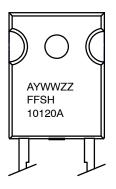


Schottky Diode



TO-247-2LD CASE 340DC

MARKING DIAGRAM



A YWW = Assembly Plant Code= Date Code (Year & Week)

ZZ

1

= Lot Code

FFSH10120A

= Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C unless otherwise noted)

Symbol	Parameter	Value	Unit	
V_{RRM}	Peak Repetitive Reverse Voltage	1200	V	
E _{AS}	Single Pulse Avalanche Energy (Note 1)	100	mJ	
I _F	Continuous Rectified Forward Current @ T _C < 158°C		10	Α
	Continuous Rectified Forward Current @ T _C <	135°C	17	
I _{F, Max}	Non-Repetitive Peak Forward Surge Current	T _C = 25°C, 10 μs	850	Α
		T _C = 150°C, 10 μs	800	Α
I _{F,SM}	Non-Repetitive Forward Surge Current	Ion-Repetitive Forward Surge Current Half-Sine Pulse, t _p = 8.3 ms		Α
I _{F,RM}	Repetitive Forward Surge Current	Half-Sine Pulse, t _p = 8.3 ms	35	Α
Ptot	Power Dissipation	T _C = 25°C	193	W
		T _C = 150°C	32	W
T _J , T _{STG}	J, T _{STG} Operating and Storage Temperature Range TO-247 Mounting Torque, M3 Screw		-55 to +175	°C
			60	Ncm

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. E_{AS} of 100 mJ is based on starting T_J = 25°C, L = 0.5 mH, I_{AS} = 20 A, V = 50 V.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{ heta JC}$	Thermal Resistance, Junction to Case, Max	0.78	°C/W

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
V _F	Forward Voltage	I _F = 10 A, T _C = 25°C	-	1.45	1.75	V
		I _F = 10 A, T _C = 125°C	-	1.7	2.0	
		I _F = 10 A, T _C = 175°C	-	2.0	2.4]
I _R	Reverse Current	V _R = 1200 V, T _C = 25°C	-	-	200	μΑ
		V _R = 1200 V, T _C = 125°C	-	-	300]
		V _R = 1200 V, T _C = 175°C	-	-	400]
Q_{C}	Total Capacitive Charge	V = 800 V	-	62	-	nC
С	Total Capacitance	V _R = 1 V, f = 100 kHz	-	612	-	pF
		V _R = 400 V, f = 100 kHz	-	58	-	
		V _R = 800 V, f = 100 kHz	-	47	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Part Number	Top Marking	Package	Shipping
FFSH10120A-F155	FFSH10120A	TO-247-2LD (Pb-Free / Halogen Free)	30 Units / Tube

TYPICAL CHARACTERISTICS

(T_J = 25°C UNLESS OTHERWISE NOTED)

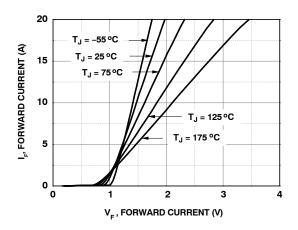


Figure 1. Forward Characteristics

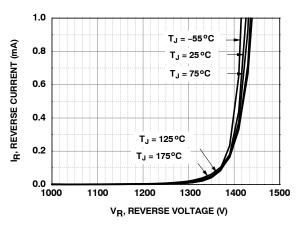


Figure 3. Reverse Characteristics

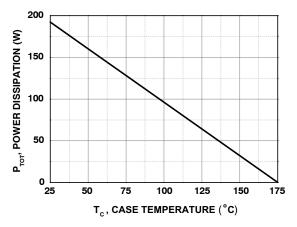


Figure 5. Power Derating

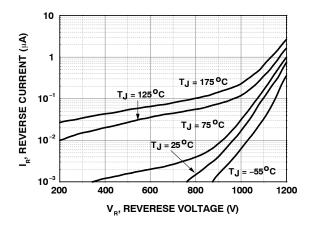


Figure 2. Reverse Characteristics

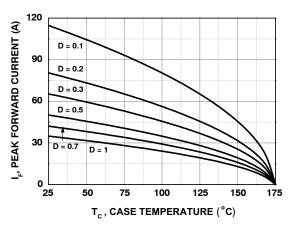


Figure 4. Current Derating

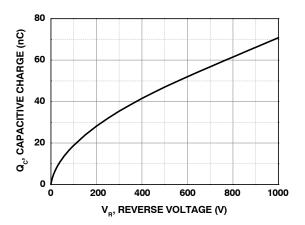
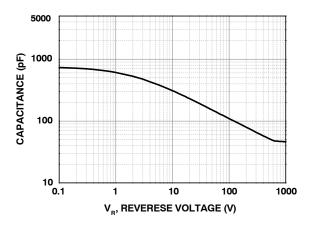


Figure 6. Capacitive Charge vs. Reverse Voltage

TYPICAL CHARACTERISTICS

(T_J = 25°C UNLESS OTHERWISE NOTED)



30 20 400 600 800 1000 V_B, REVERVE VOLTAGE (V)

Figure 7. Capacitance vs. Reverse Voltage

Figure 8. Capacitance Stored Energy

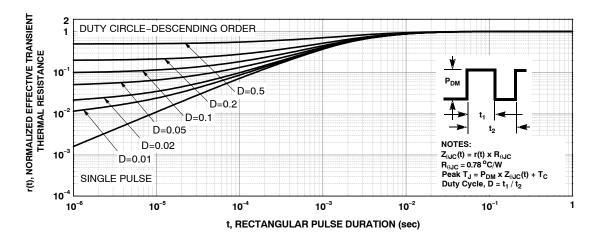


Figure 9. Junction-to-Case Transient Thermal Response Curve

TEST CIRCUIT AND WAVEFORMS

L = 0.5 mH $R < 0.1 \Omega$ $V_{DD} = 50 \text{ V}$ $EAVL = 1/2L12 \left[V_{R(AVL)} / (V_{R(AVL)} - V_{DD})\right]$ $Q1 = IGBT \left(BV_{CES} > DUT \ V_{R(AVL)}\right)$ $CURRENT V_{DD}$ V_{DD}

 $V_{DD} \\$

DUT

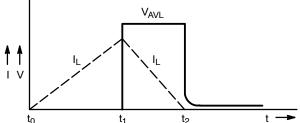
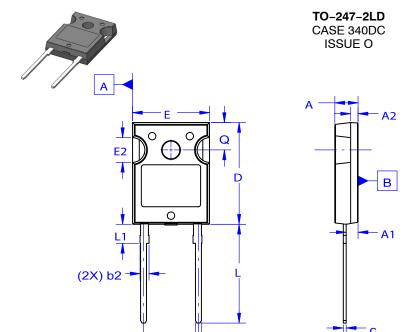
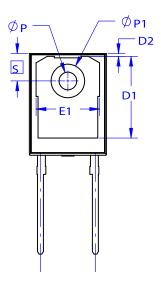


Figure 10. Unclamped Inductive Switching Test Circuit & Waveform



DATE 09 JUL 2020



NOTES:

A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.

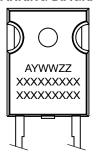
(2X) b

0.25 M B A M

- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSION AND TOLERANCE AS PER ASME Y14.5-2009.
- D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

DIM	MILLIMITERS			
DIM	MIN	NOM	MAX	
Α	4.58	4.70	4.82	
A 1	2.20	2.40	2.60	
A2	1.40	1.50	1.60	
b	1.17	1.26	1.35	
b2	1.60	1.72	1.84	
С	0.51	0.61	0.71	
D	20.32	20.57	20.82	
D1	13.08	~	~	
D2	0.51	0.93	1.35	
Е	15.37	15.62	15.87	
E1	12.81	~	~	
E2	4.96	5.08	5.20	
е	~	11.12	~	
L	19.75	20.00	20.25	
L1	3.69	3.81	3.93	
<u> </u>	3.51	3.58	3.65	
Ø P 1	6.60	6.80	7.00	
Q	5.34	5.46	5.58	
S	5.34	5.46	5.58	

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code

A = Assembly Location Y = Year

WW = Work Week
ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb—Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	TO-247-2LD		PAGE 1 OF 1	

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